

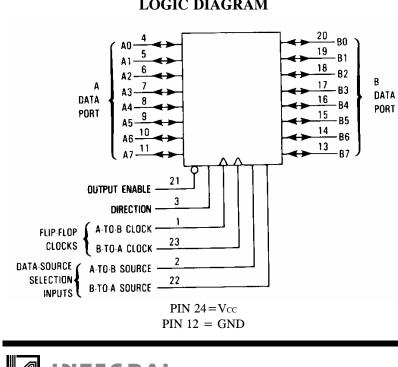
Octal 3-State Bus Transceivers and D Flip-Flops **High-Performance Silicon-Gate CMOS**

The IN74HC651 is identical in pinout to the LS/ALS651. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LS/ALSTTL outputs.

These devices consists of bus transceiver circuits, D-type flipflop, and control circuitry arranged for multiplex transmission of data directly from the data bus or from the internal storage registers. Direction and Output Enable are provided to select the read-time or stored data function. Data on the A or B Data bus, or both, can be stored in the internal D flip-flops by low-to-high transitions at the appropriate clock pins (A-to-B Clock or B-to-A Clock) regardless of the select or enable or enable control pins. When A-to-B Source and B-to-A Source are in the real-time transfer mode, it is also possible to store data without using the internal D-type flip-flops by simultaneously enabling Direction and Output Enable. In this configuration each output reinforces its input. Thus, when all other data sources to the two sets of bus lines are at high impedance, each set of bus lines will remain at its last state.

The IN74HC651 has inverted outputs.

- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 µA
- High Noise Immunity Characteristic of CMOS Devices



LOGIC DIAGRAM

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PIN ASSIGNMENT

	A-TO-B CLOCK	Ľ	1•	24	þ	V _{CC}
	A-TO-B SOURCE	Ľ	2	23	þ	B-TO-A CLOCK
DIF	RECTION	Ľ	3	22	þ	B-TO-A SOURCE
	A0	Ľ	4	21	þ	OUTPUT ENABLE
	A1	Ľ	5	20	þ	B0
	A2	Ľ	6	19	þ	B 1
	A3	Ľ	7	18	þ	B2
	A4	Ľ	8	17	þ	B3
	A5	Ľ	9	16	þ	B4
	A6	Ľ	10	15	þ	B5
	A7	Ľ	11	14	þ	B6
ATA	GND	Ľ	12	13	Þ	B7

Symbol	Parameter	Value	Unit
Vcc	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
Vin	DC Input Voltage (Referenced to GND)	-1.5 to Vcc +1.5	V
Vout	DC Output Voltage (Referenced to GND)	-0.5 to Vcc +0.5	V
IIN	DC Input Current, per Pin	±20	mA
Iout	DC Output Current, per Pin	±35	mA
Icc	DC Supply Current, Vcc and GND Pins	±75	mA
PD	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
Tstg	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

+Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: : - 7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
Vcc	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
VIN, VOUT	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	V
TA	Operating Temperature, All Package Types	-55	+125	°C
tr, tf	Input Rise and Fall Time (Figures 2,3) $V_{CC} = 2.0 V$ $V_{CC} = 4.5 V$ $V_{CC} = 6.0 V$	0 0 0	1000 500 400	ns

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND \leq (V_{IN} or V_{OUT}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or Vcc). Unused outputs must be left open. I/O pins must be connected to a properly terminated line or bus.

INTEGRAL

			Vcc	Guaranteed Limit			
Symbol	Parameter	Test Conditions	V	25 °C to -55°C	≤85 °C	≤125 °C	Unit
VIH	Minimum High- Level Input Voltage	Vout=0.1 V or Vcc-0.1 V Iout $\leq 20 \ \mu A$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
VIL	Maximum Low - Level Input Voltage	Vout=0.1 V or Vcc-0.1 V Iout $\leq 20 \ \mu A$	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
Vон	Minimum High- Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \ \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 6.0 \text{ mA}$ $ I_{OUT} \le 7.8 \text{ mA}$	4.5 6.0	3.98 5.48	3.84 5.34	3.7 5.2	
Vol	Maximum Low- Level Output Voltage	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $ I_{OUT} \le 20 \ \mu A$	2.0 4.5 6.0	$0.1 \\ 0.1 \\ 0.1$	$0.1 \\ 0.1 \\ 0.1$	$0.1 \\ 0.1 \\ 0.1$	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 6.0 \text{ mA}$ $ I_{OUT} \le 7.8 \text{ mA})$	4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	
IIN	Maximum Input Leakage Current	V _{IN} =V _{CC} or GND (Pins 1,2,3,21,22,and 23)	6.0	±0.1	±1.0	±1.0	μΑ
Ioz	Maximum Three- State Leakage Current	Output in High-Impedance State $V_{IN} = V_{IL}$ or V_{IH} $V_{OUT} = V_{CC}$ or GND, I/O Pins	6.0	±0.5	±5.0	±10	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	V _{IN} =V _{CC} or GND Iout=0µA	6.0	8.0	80	160	μΑ

DC ELECTRICAL CHARACTERISTICS(Voltages Referenced to GND)



		Vcc	Gu			
Symbol	Parameter	v	25 °C	≤85°C	≤125°C	Unit
			to			
			-55°C			
tplh, tphl	Maximum Propagation Delay, Input A to Output	2.0	180	225	270	ns
	B (or Input B to Output A)	4.5	36	45	54	
	(Figures 2,3 and 9)	6.0	31	38	46	
tplh, tphl	Maximum Propagation Delay, A-to-B Clock to	2.0	240	300	360	ns
	Output B (or B-to-A Clock to Output A)	4.5	48	60	72	
	(Figures 1 and 9)	6.0	41	51	61	
tplh, tphl	Maximum Propagation Delay, A-to-B Source to	2.0	220	275	330	ns
	Output B (or B-to-A Source to Output A)	4.5	44	55	66	
	(Figures 4 and 9)	6.0	37	47	56	
tplz, tphz	Maximum Propagation Delay, Direction or	2.0	170	215	255	ns
	Output Enable to Output A or B	4.5	34	43	51	
	(Figures 5,6 and 10)	6.0	29	37	43	
tpzl, tpzh	Maximum Propagation Delay, Direction or	2.0	180	225	270	ns
	Output Enable to Output A or B	4.5	36	45	54	
	(Figures 5,6 and 10)	6.0	31	38	46	
ttlh, tthl	Maximum Output Transition Time, Any Output	2.0	60	75	90	ns
	(Figure 2)	4.5	12	15	18	
		6.0	10	13	15	
Cin	Maximum Input Capacitance	-	10	10	10	pF
Cout	Maximum Three-State I/O Capacitance	-	15	15	15	pF
	(Output in High-Impedance State					
	1	1				
	Down Dissingtion Consolitance (Der Channel)				5 O V	1

AC ELECTRICAL CHARACTERISTICS(CL=50pF,Input tr=tf=6.0 ns)

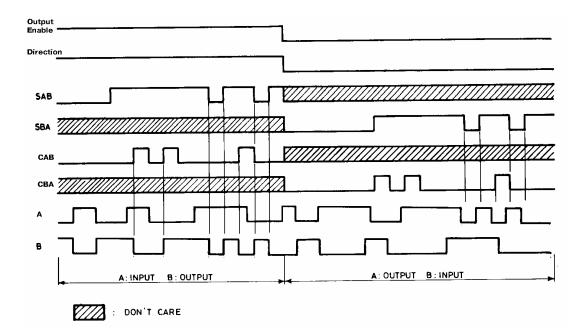
	Power Dissipation Capacitance (Per Channel)	Typical @25°C,Vcc=5.0 V	
Cpd	Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$	60	pF



		Vcc	Guara			
Symbol	Parameter	V	25 °C to-55°C	≤85°C	≤125°C	Unit
tsu	Minimum Setup Time, Input A to A-to-B Clock (or Input B to B-to-A Clock) (Figure 7)	2.0 4.5 6.0	50 10 9	65 13 11	75 15 13	ns
th	Minimum Hold Time, A-to-B Clock to Input A (or B-to-A Clock to Input B) (Figure 7)	2.0 4.5 6.0	25 5 5	30 6 5	40 8 7	ns
tw	Minimum Pulse Width, A-to-B Clock (or B-to-A Clock) (Figure 7)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
tr, tf	Maximum Input Rise and Fall Times (Figures 2 and 3)	2.0 4.5 6.0	1000 500 400	1000 500 400	1000 500 400	ns

TIMING REQUIREMENTS(Input tr=tf=6.0 ns)

TIMING DIAGRAM





IN74HC651

Dir.	OE	CAB	CBA	SAB	SBA	A	B	FUNCTION
						INPUTS	INPUTS	Both the A bus and the B bus are inputs.
L	Н	Х	Х	Х	Х	Z	Z	The output functions of the A and B bus are disabled.
		L-	۲	Х	Х	INPUTS	INPUTS	Both the A and B bus are used for inputs to the internal flip-flops. Data at the bus will be stored on low to high transition of the clock inputs.
						OUTPUTS	INPUTS	The A bus are outputs and the B bus are inputs.
		\mathbf{X}^*	X	Х	L	H L	L H	The data at the B bus are displayed at the A bus.
L	L	X*	ام ^ا	Х	L	H L	L H	The data at the B bus are displayed at the A bus. The data of the B bus are stored to the internal flip-flops on low to high transition of the clock pulse.
		X*	Х	Х	Н	Qn	Х	The data stored to the internal flip-flops, are displayed at the A bus.
		X*	لم	Х	Η	L H	H L	The data at the B bus are stored to the internal flip-flops on low to high transition of the clock pulse. The states of the internal flip-flops output directly to the A bus.
						INPUTS	OUTPUTS	The A bus are inputs and the B bus are outputs.
		X	\mathbf{X}^*	L	Х	H L	L H	The data at the A bus are displayed at the B bus.
Н	Η	الم	X*	L	Х	H L	L H	The data at the B bus are displayed at the A bus. The data of the B bus are stored to the internal flip-flops on low to high transition of the clock pulse.
		Х	\mathbf{X}^{*}	Η	Х	Х	Qn	The data stored to the internal flip-flops are displayed at the B bus.
		لم	X*	Η	Х	H L	L H	The data at the A bus are stored to the internal flip-flops on low to high transition of the clock pulse. The states of the internal flip-flops output directly to the B bus.
						OUTPUTS	OUTPUTS	Both the A bus and the B bus are outputs
Н	L	Х	Х	Н	Н	Qn	Qn	The data stored to the internal flip-flops are displayed at the A and B bus respectively.
		₽	_	Н	Н	Qn	Qn	The output at the A bus are displayed at the B bus, the output at the B bus are displayed at the A bus respec.

FUNCTION TABLE

X : DON'T CARE

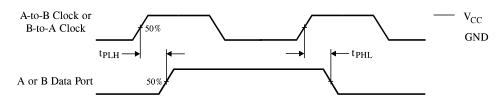
Z : HIGH IMPEDANCE

Qn : THE DATA STORED TO THE INTERNAL FLIP-FLOPS BY MOST RECENT LOW TO HIGH TRANSITION OF THE CLOCK INPUTS

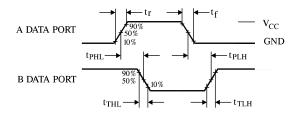
 * : THE DATA AT THE A AND B BUS WILL BE STORED TO THE INTERNAL FLIP-FLOPS ON EVERY LOW TO TRANSITION OF THE CLOCK INPUTS

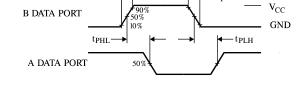


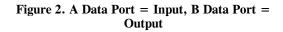
SWITCHING DIAGRAMS

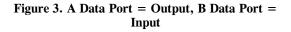












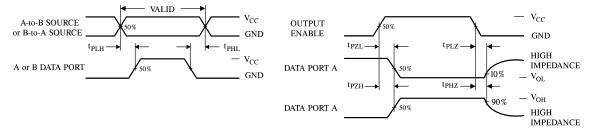
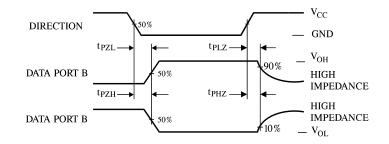
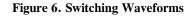


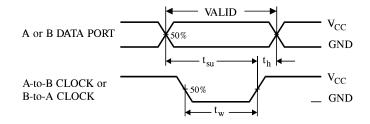
Figure 4. Switching Waveforms













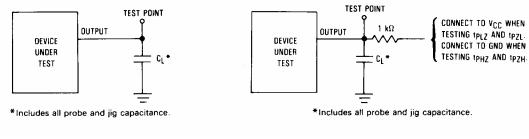
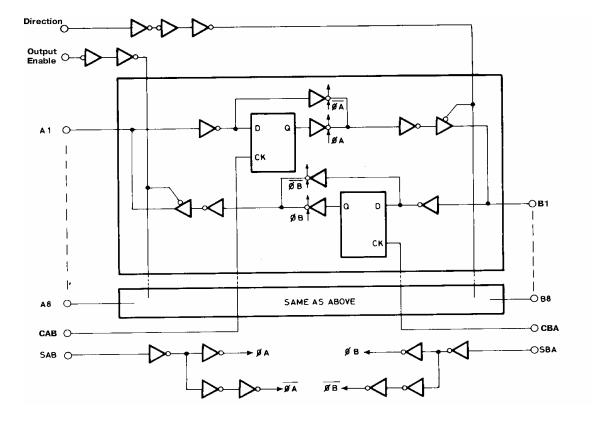


Figure 9. Test Circuit

Figure 10. Test Circuit





EXPANDED LOGIC DIAGRAM

